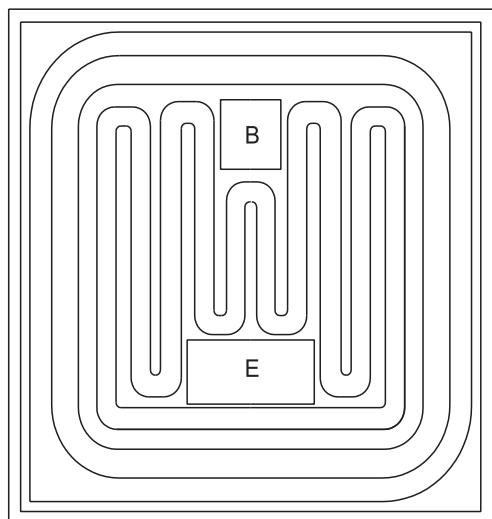


# PRELIMINARY

## PROCESS DETAILS

|                          |                  |
|--------------------------|------------------|
| Process                  | EPITAXIAL PLANAR |
| Die Size                 | 30 x 30 MILS     |
| Die Thickness            | 9.0 MILS         |
| Base Bonding Pad Area    | 3.85 x 4.20 MILS |
| Emitter Bonding Pad Area | 7.35 x 3.75 MILS |
| Top Side Metalization    | Al - 30,000Å     |
| Back Side Metalization   | Au - 15,000Å     |

## GEOMETRY



BACKSIDE COLLECTOR

## GROSS DIE PER 4 INCH WAFER

12,300

## PRINCIPAL DEVICE TYPES

2N3467

2N3468

R0

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R0 (24-June 2003)